

A HI Flexible High Resolution μ Display Enabled By FlexTrate™

Henry Sun¹, Lisong Xu², Kai Ding², Mingwei Zhu², and Subramanian S. Iyer¹

¹UCLA CHIPS, ²Applied Materials Inc

Hsunhenry@ucla.edu

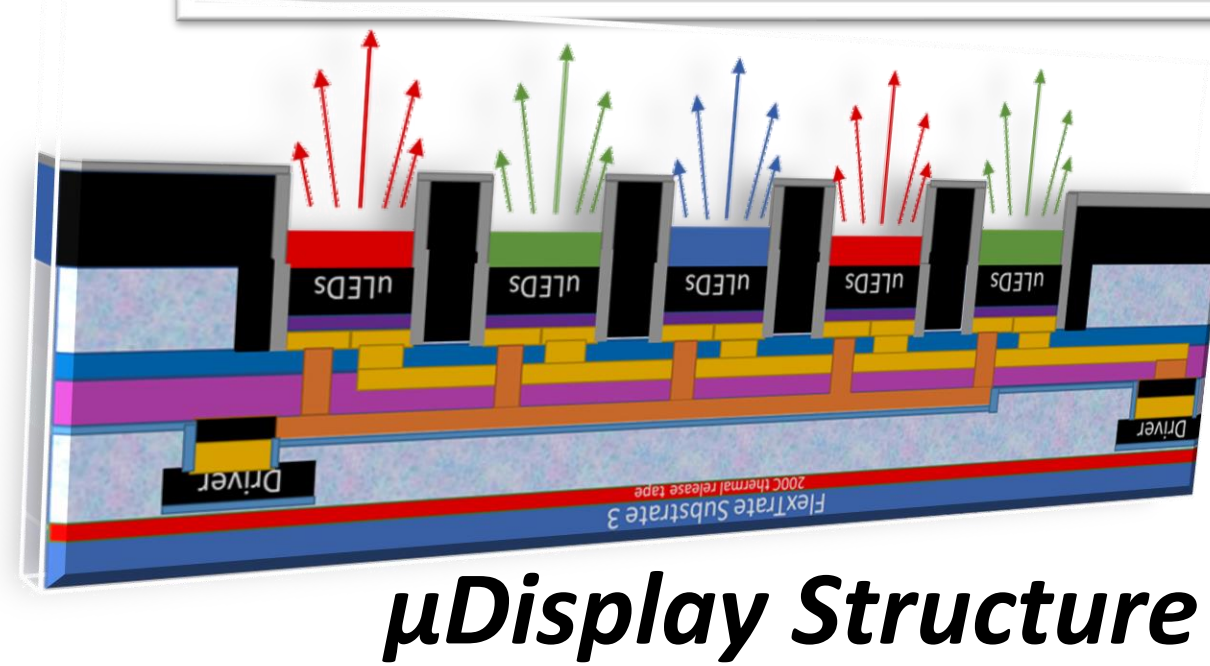
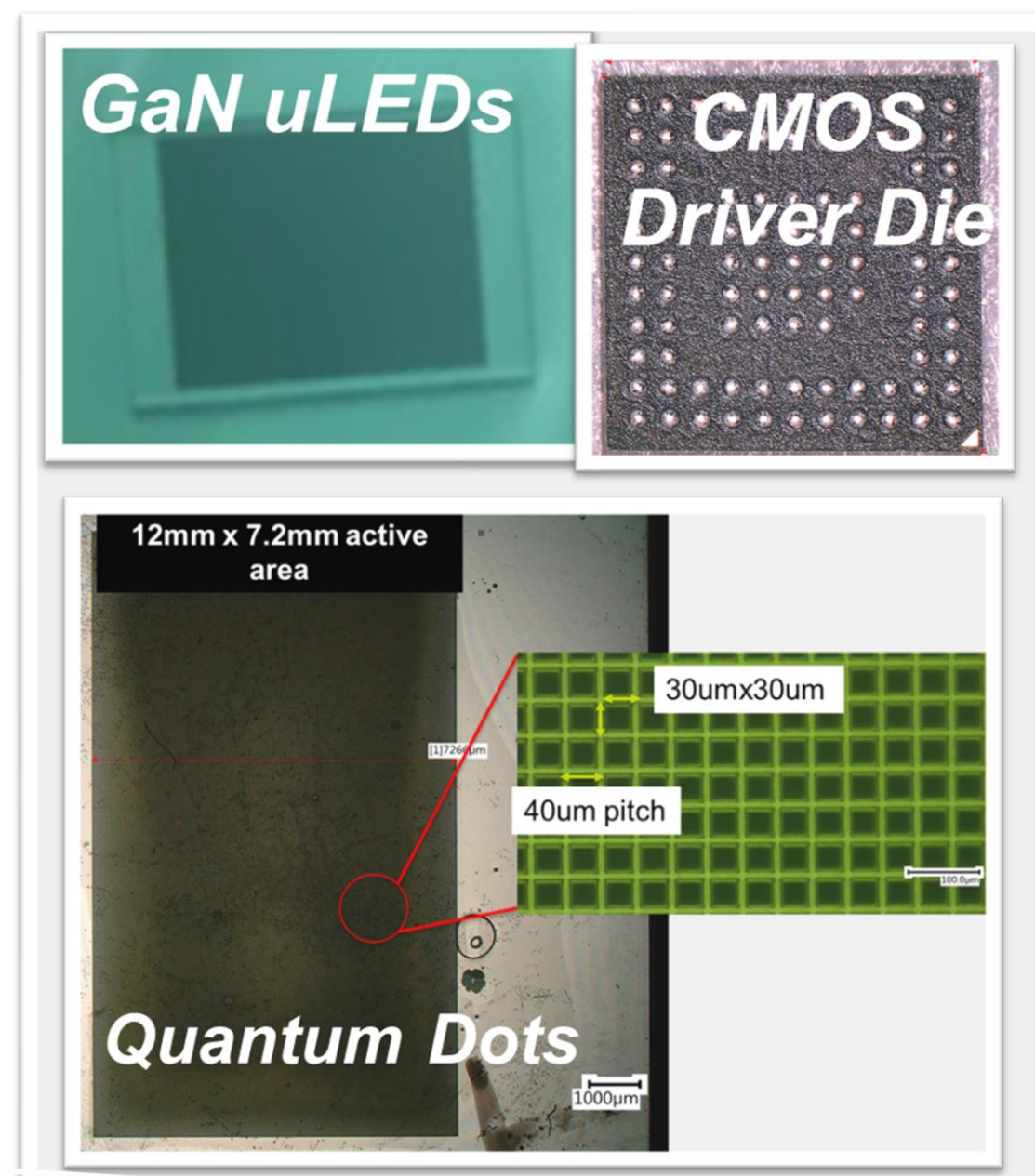
Introduction and Motivation

Novel approach to create Quantum dot-enabled, flexible, μ Displays using FlexTrate™ Featuring:

- GaN μ LEDs: High brightness (>5000nits), high hi resolution (>600PPI in 360x280 resolution)
- High Performance CMOS driver for passive matrix display (TLC6984)
- Quantum Dots to convert monochrome LED to RGB subpixels (<10 μ m thick QD layer)
- FlexTrate™ Platform for Heterogeneous Integration

Key Benefits:

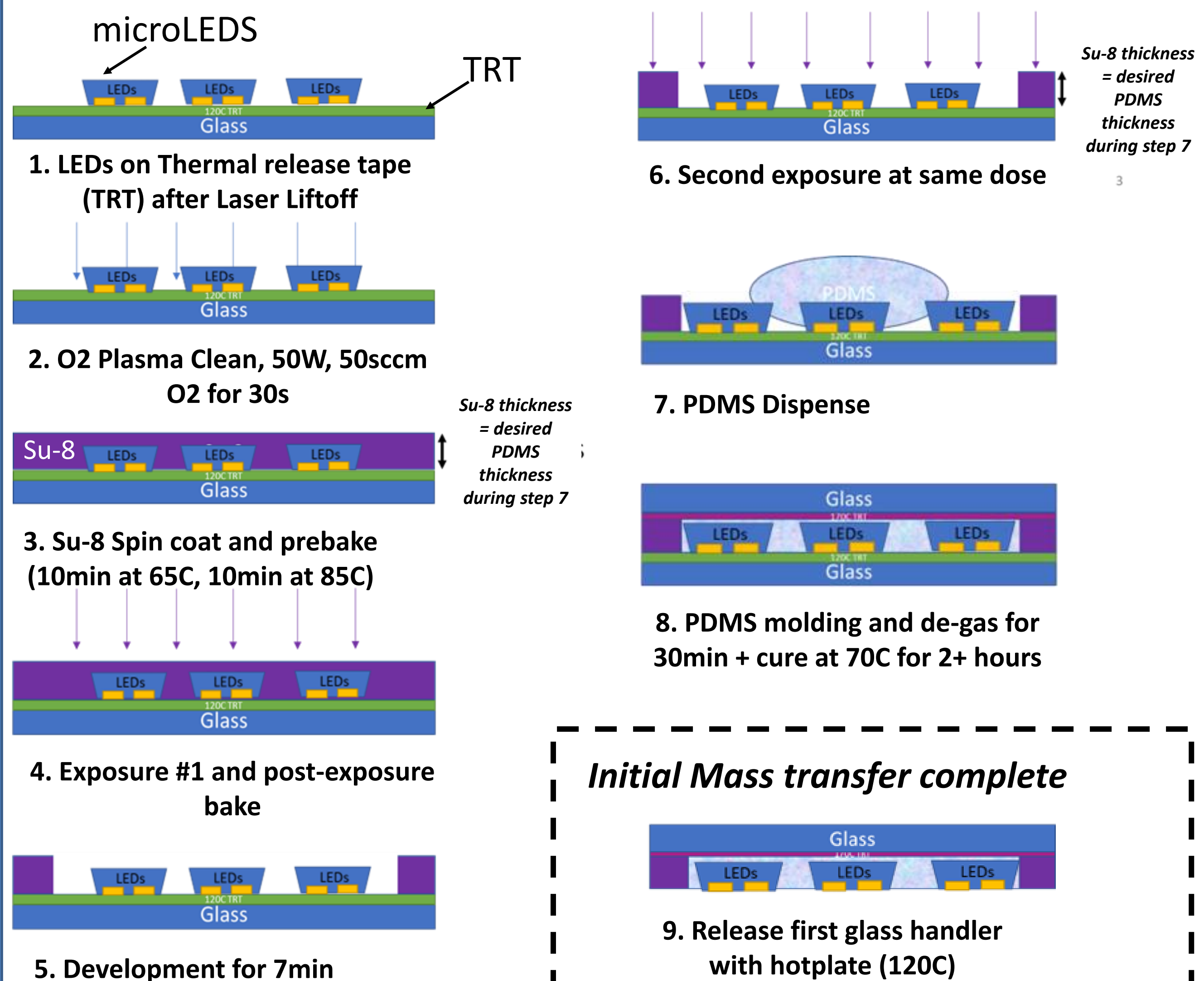
- Light weight, High Flexibility
- Long display lifetime (10 years+)
- Substantial increase in manufacturability
- Agnostic to die thickness and material type



μ Display Structure

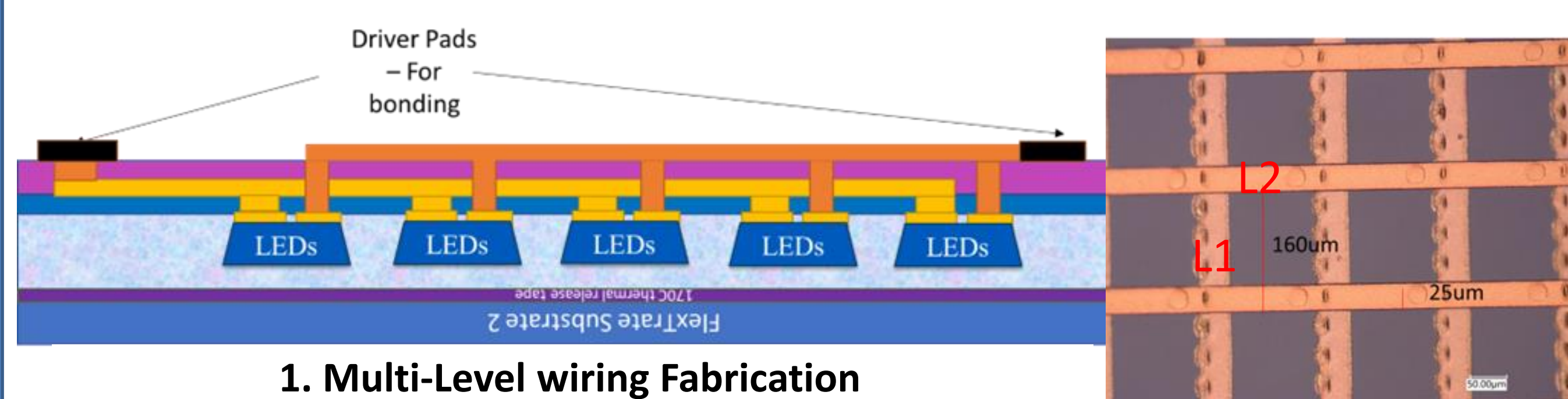
Fabrication Process Flow for μ LED Display

Mass Transfer onto Flexible PDMS substrate



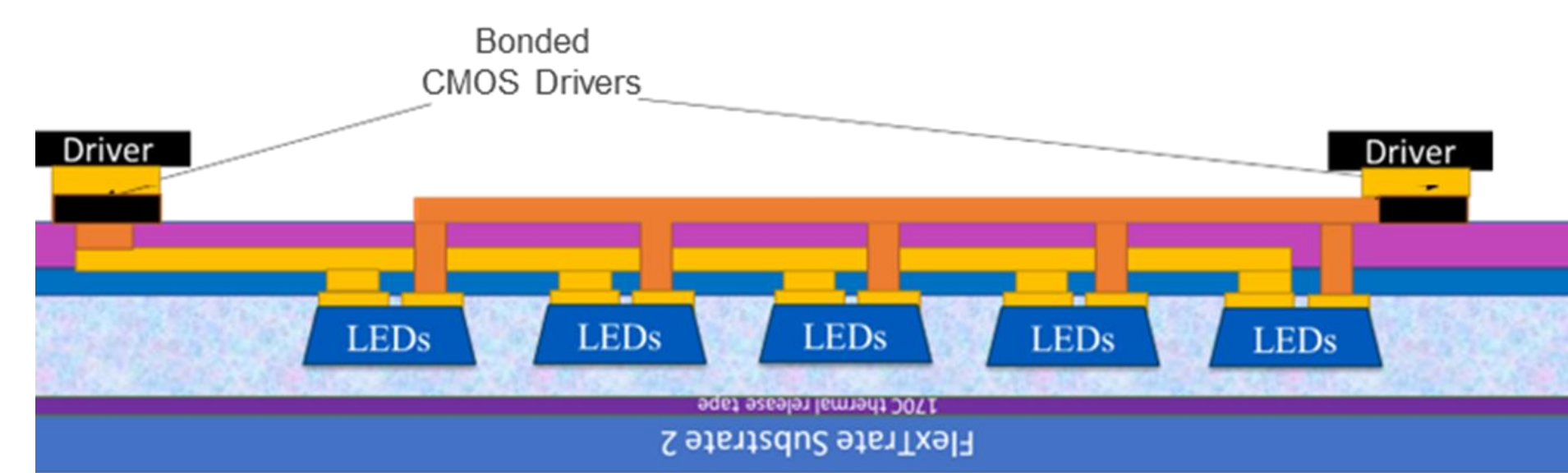
High throughput and high yield (>99.99%)

Wire fabrication and Driver, Quantum Dot Integration

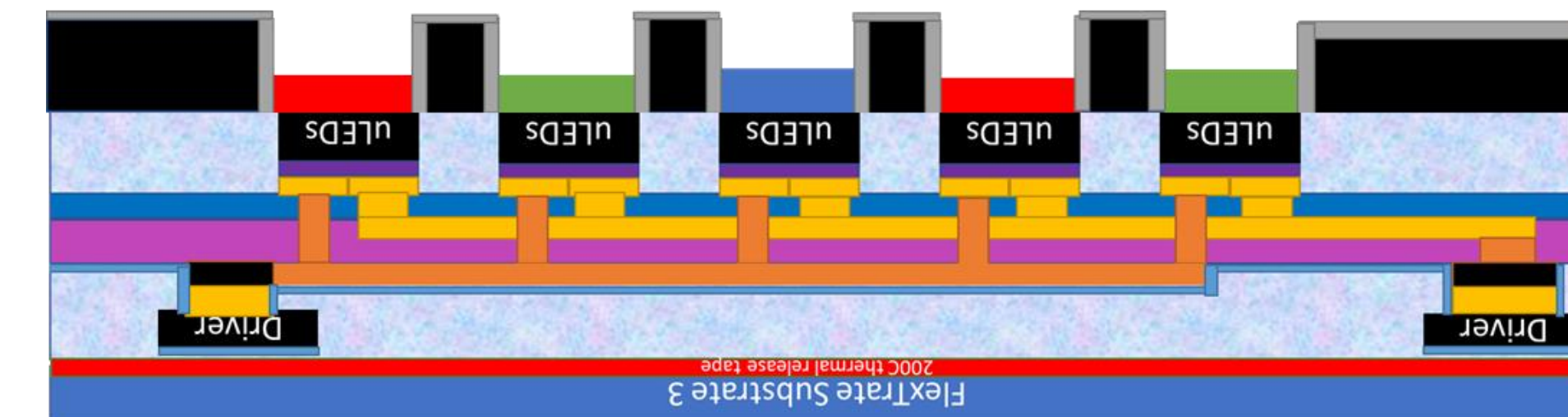


1. Multi-Level wiring Fabrication

Bonding of Drivers and Quantum Dot Integration



2. Flip-chip bonded driver chips



3. Final Structure with Quantum Dot (QD) dispense

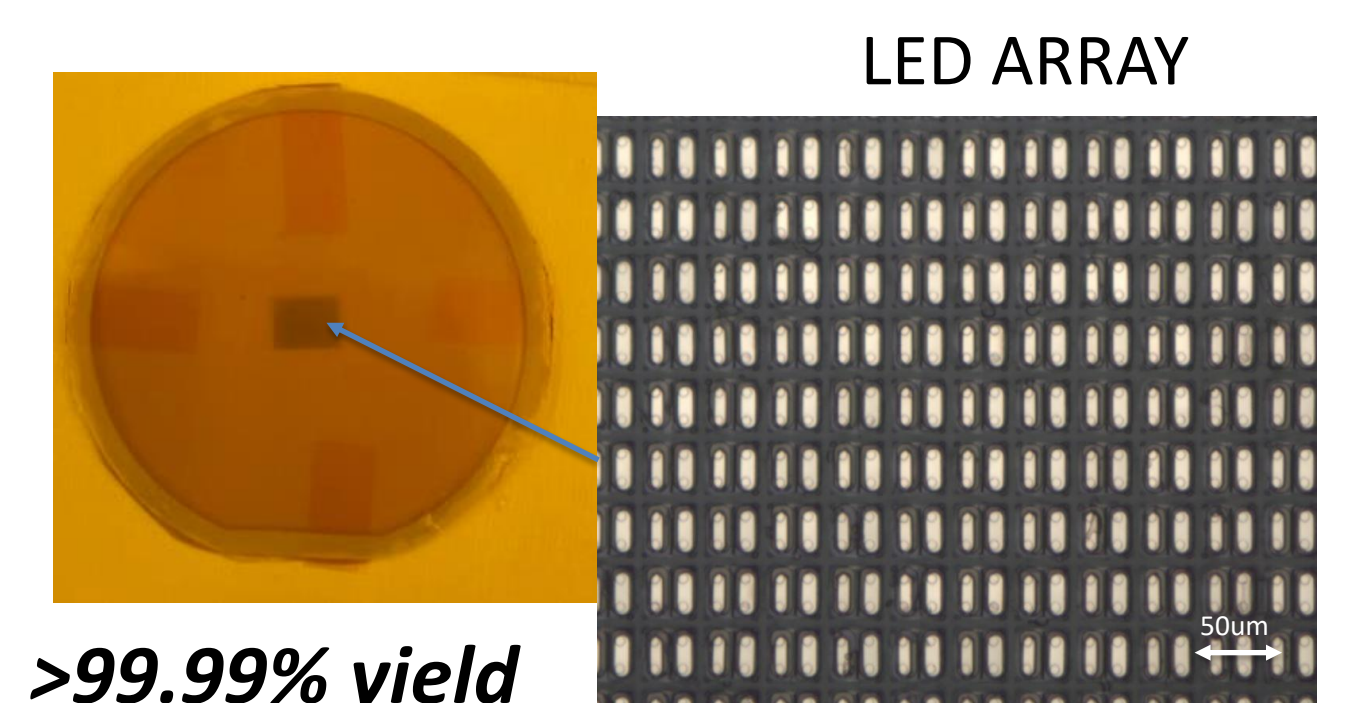
CMOS drivers and passive components are flip-chip bonded onto the driver pads using K&S APAMA flip-chip bonder

Quantum dots are dispensed onto a scaffold structure embedded in PDMS to prevent pixel-pixel optical crosstalk

Results And Discussion

Mass transfer results

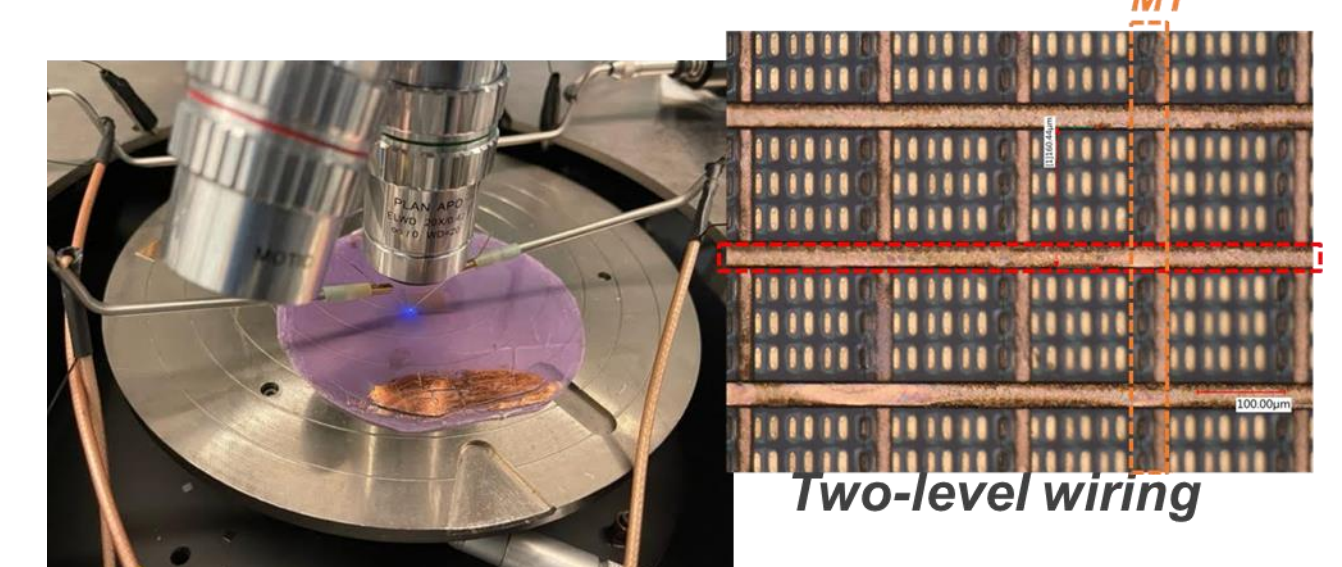
- ~100,000 dies transferred at >99.99% yield
- 361 x 284 pixels
- 30 μ m pixels at 40 μ m pitch
- High degrees of flexibility <3mm bending radius after molding on flexible substrate



>99.99% yield

Two-level wiring grid design

- M1 layer addresses the n-contacts of LEDs while M2 layer addresses the p-contacts
- Individual LEDs turn on at 3.01V
- Process optimization to maintain uniform, low resistance across individual wires



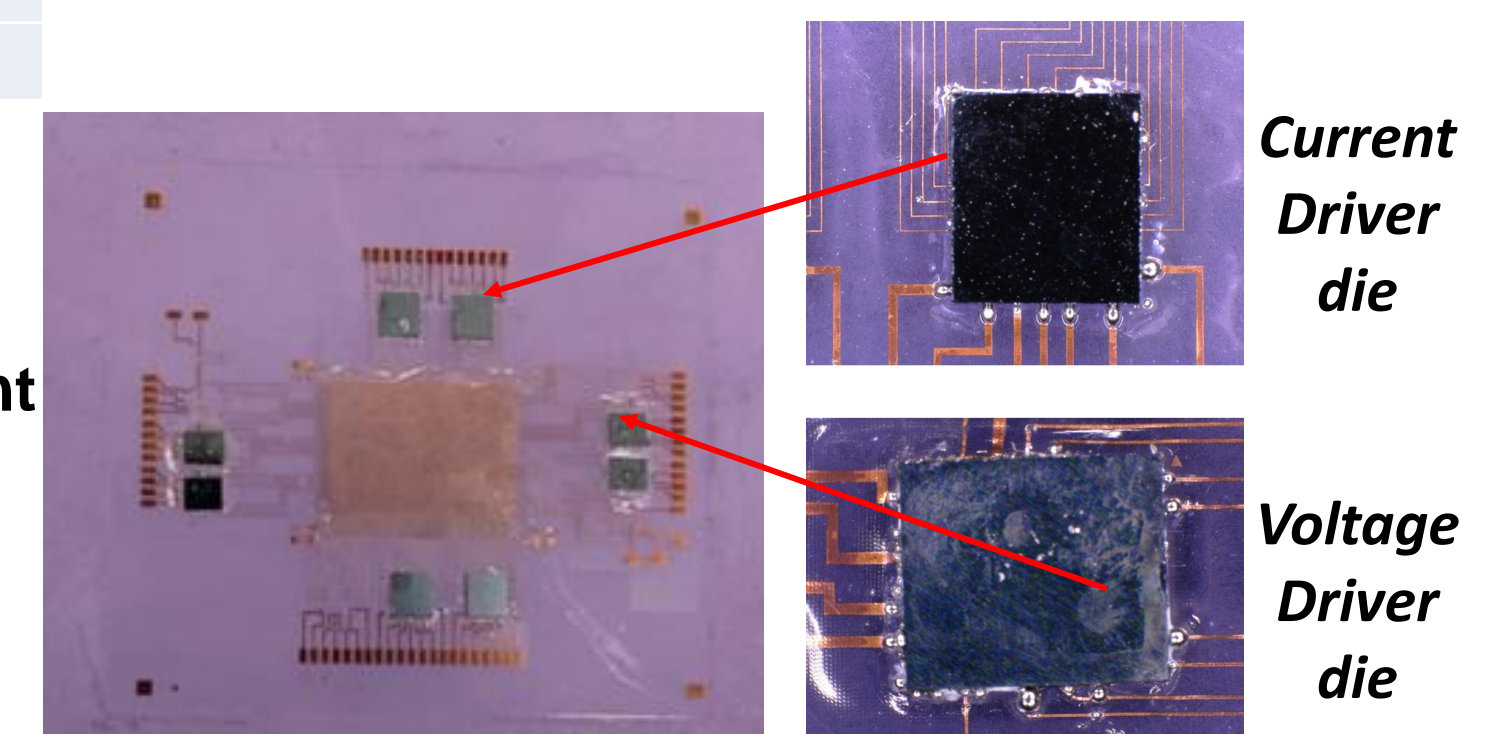
M1 Resistance Measurements

Section	Average Ω	σ
A	6.2	1.04
B	4.4	2.1
C	4.1	1.78
D	5.6	2.2
E	6.3	2.54

Section	Average Ω	σ
A	13.2	1.6
B	10.1	3.1
C	14.6	2.87
D	12.02	3.04
E	12.2	1.79

Driver integration

- Bonding of 2.5mm x 3mm current and 3mm x 3.5mm voltage drivers using flip chip bonder (K&S APAMA) on driver pads



Current Driver die

Voltage Driver die

Conclusion and Acknowledgements

- Demonstrated a method of fabricating a high performance, flexible μ Display on FlexTrate™
- Demonstrated high yield and throughput during initial transfer step
- We thank our partners at Applied Materials and members of the UCLA CHIPS consortium for their generous support on this project.
- We also acknowledge the UCLA Nanoelectronics Research Facilities and Integrated Systems Nanofabrication Cleanroom and staff.